CLAIMS

What is claimed is:

1. A fabrication method of an acoustic wave device comprising:

forming a metal layer between regions that are located on a piezoelectric substrate and in which acoustic wave chips are to be formed, at least a part of a region of the metal layer extending to an extension direction of a dicing line for separating the acoustic wave chips; and

scanning the dicing line of the piezoelectric substrate by a laser beam so that the at least a part of the region of the metal layer is not irradiated with the laser beam~~.~~,

wherein the metal layer includes:

a first region, which is the at least a part of the region of the metal layer and is located at one side of the dicing line;

a second region, which is the at least a part of the region of the metal layer and is located at another side of the dicing line; and

a third region connecting the first region to the second region between the regions in which acoustic wave chips are to be formed, and being not located between IDTs formed on the piezoelectric substrate,

wherein the first region and the second region are located so as not to overlap each other in the extension direction.

~~2. The fabrication method of the acoustic wave device according to claim 1, wherein~~

~~the metal layer continuously extends to an edge portion of the piezoelectric substrate.~~

~~3. The fabrication method of the acoustic wave device according to claim 1 or 2, wherein~~

~~the metal layer includes a first region, which is the at least a part of the region of the metal layer and is located at one side of the dicing line, and a second region, which is the at least a part of the region of the metal layer and is located at another side of the dicing line.~~

~~4. The fabrication method of the acoustic wave device according to claim 3, wherein~~

~~the metal layer includes a third region connecting the first region to the second region.~~

~~5. The fabrication method of the acoustic wave device according to claim 4, wherein~~

~~the first region and the second region are located so as not to overlap each other in the extension direction.~~

~~6. The fabrication method of the acoustic wave device according to claim 4 or 5, wherein~~

~~the third region is not located between IDTs formed on the piezoelectric substrate.~~

~~7. The fabrication method of the acoustic wave device according to claim 1 or 2, wherein~~

~~the metal layer is formed at only one side of the dicing line.~~

~~8. The fabrication method of the acoustic wave device according to claim 3 or 7, wherein~~

~~the metal layer has a straight line shape.~~

~~9~~2. The fabrication method of the acoustic wave device according to ~~any one of claims 1 through 8~~ claim 1, further comprising:

separating the acoustic wave chips into individual ones along the dicing line.